19-2946: Rev 0: 9/03

MIXIM

-48V Hot-Swap Controllers with External RSENSE and High Gate Pulldown Current

General Description

The MAX5921/MAX5939 hot-swap controllers allow a circuit card to be safely hot plugged into a live backplane. The MAX5921/MAX5939 operate from -20V to -80V and are well suited for -48V power systems. These devices are pin compatible with both the LT1640 and LT4250 and provide improved features over these devices.

The MAX5921/MAX5939 provide a controlled turn-on to circuit cards preventing damage to board connectors, board components, and preventing glitches on the power-supply rail. The MAX5921/MAX5939 provide undervoltage, overvoltage, and overcurrent protection. These devices ensure that the input voltage is stable and within tolerance before applying power to the load.

Both the MAX5921 and MAX5939 protect a system against overcurrent and short-circuit conditions by turning off the external MOSFET in the event of a fault condition. The MAX5921/MAX5939 protect against input voltage steps by limiting the load current to a safe level without turning off power to the load.

The device features an open-drain power-good status output, PWRGD or PWRGD for enabling downstream converters (see Selector Guide). A built-in thermal shutdown feature is also included to protect the external MOSFET in case of overheating. The MAX5939 features a latched fault output. The MAX5921 contains built-in autoretry circuitry after a fault condition.

The MAX5921/MAX5939 are available in an 8-pin SO package and operate in the extended -40°C to +85°C temperature range.

Applications

Telecom Line Cards Network Switches/Routers Central-Office Line Cards Server Line Cards Base-Station Line Cards

Typical Operating Circuit and Selector Guide appear at end of data sheet.

Features

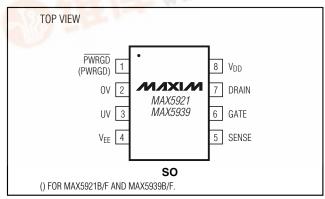
- ♦ Allows Safe Board Insertion and Removal from a Live -48V Backplane
- ◆ Pin-Compatible with LT1640 and LT4250
- ♦ Circuit Breaker Immunity to Input Voltage Steps and Current Spikes
- ♦ 450mA GATE Pulldown Current During Short-**Circuit Condition**
- **♦ Exponential GATE Pulldown Current**
- ♦ Withstands -100V Input Transients with No External Components
- Programmable Inrush and Short-Circuit Current Limits
- ♦ Operates from -20V to -80V
- ♦ Programmable Overvoltage Protection
- ♦ Programmable Undervoltage Lockout with Built-In Glitch Filter
- ♦ Overcurrent Fault Integrator
- ♦ Powers Up into a Shorted Load
- ♦ Power-Good Control Output
- Thermal Shutdown Protects External MOSFET

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX5921AESA	-40°C to +85°C	8 SO
MAX5921BESA	-40°C to +85°C	8 SO

Ordering Information continued at end of data sheet.

Pin Configuration



Maxim Integrated Products 1

ABSOLUTE MAXIMUM RATINGS

ess Otherwise Noted
0.3V to +100V
0.3V to +100V
0.3V to +95V
95V to +85V
0.3V to +1.0V
0.3V to +18V
0.3V to +60V
+40mA

Current into GATECurrent into Any Other Pin	
Continuous Power Dissipation ($TA = +70^{\circ}C$)	
8-Pin SO (derate 5.9mW/°C above +70°C)	471mW
Operating Temperature Range	40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(VEE = 0V, VDD = 48V, TA = -40°C to +85°C, unless otherwise noted. Typical values are at TA = +25°C, unless otherwise noted.) (Notes 1, 4)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
POWER SUPPLIES	•					
Operating Input Voltage Range	V_{DD}		20		80	V
Supply Current	I _{DD}	Current into V _{DD} with UV = 3V, OV, DRAIN, SENSE = V _{EE} , GATE = floating		0.7	2	mA
GATE DRIVER AND CLAMPING	CIRCUITS					
Gate Pullup Current	I _{PU}	GATE drive on, VGATE = VEE	-30	-45	-60	μΑ
Gate Pulldown Current	IPD	V _{SENSE} - V _{EE} = 100mV, V _{GATE} = 2V (Note 2)	24	50	70	mA
External Gate Drive	ΔVGATE	V _{GATE} - V _{EE} , steady state, 20V ≤ V _{DD} ≤ 80V	10	13.5	18	V
GATE to VEE Clamp Voltage	VGSCLMP	V _{GATE} - V _{EE} , I _{GS} = 30mA	15	16.4	18	V
CIRCUIT BREAKER						
Current-Limit Trip Voltage	V _C L	V _{CL} = V _{SENSE} - V _{EE}	40	50	60	mV
SENSE Input Current	ISENSE	V _{SENSE} = 50mV	-1	-0.2	0	μΑ
UNDERVOLTAGE LOCKOUT						
Supply Internal Undervoltage Lockout Voltage High	Vuvloh	V _{DD} increasing	13.8	15.4	17.0	V
Supply Internal Undervoltage Lockout Voltage Low	V _U VLOL	V _{DD} decreasing	11.8	13.4	15.0	V
UV INPUT	•					
UV High Threshold	V _{UVH}	UV voltage increasing	1.240	1.255	1.270	V
UV Low Threshold	V _{UVL}	UV voltage decreasing	1.105	1.125	1.145	V
UV Hysteresis	Vuvhy			130		mV
UV Input Current	I _{INUV}	UV = VEE	-0.5		0	μΑ
OV INPUT						
OV High Threshold	Vovh	OV voltage rising	1.235	1.255	1.275	V
OV Low Threshold	V _{OVL}	OV voltage decreasing	1.189	1.205	1.221	V
OV Voltage Reference Hysteresis	Vovhy			50		mV
OV Input Current	I _{INOV}	$OV = V_{EE}$	-0.5		0	μΑ

ELECTRICAL CHARACTERISTICS (continued)

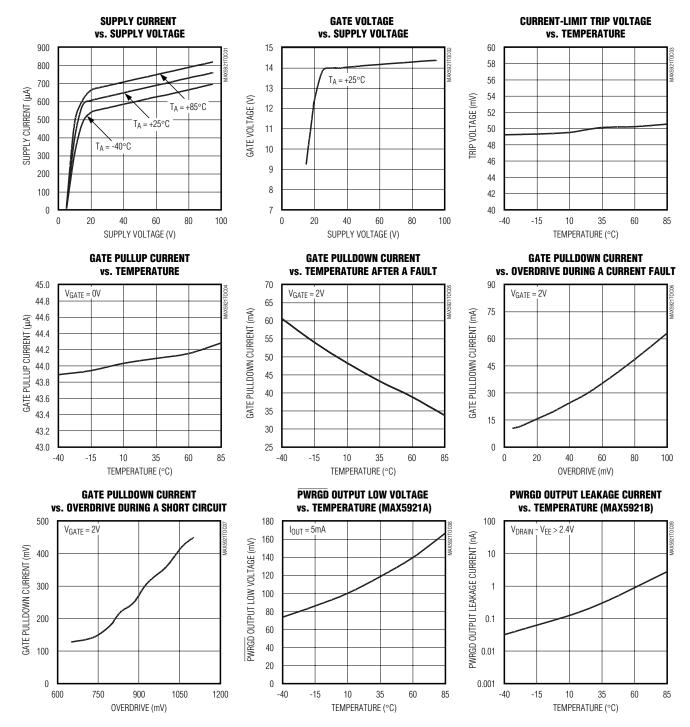
(VEE = 0V, VDD = 48V, TA = -40°C to +85°C, unless otherwise noted. Typical values are at TA = +25°C, unless otherwise noted.) (Notes 1, 4)

PARAMETER	SYMBOL	CONDITIONS			MIN	TYP	MAX	UNITS
PWRGD OUTPUT SIGNAL (REFE	RENCED TO	DRAIN)						
DRAIN Input Current	IDRAIN	V _{DRAIN} = 48V			10	80	250	μΑ
DRAIN Threshold for PWRGD	V _{DL}	V _{DRAIN} - V _{EE} threshold fo condition, DRAIN decrease		ver-good	1.1	1.7	2.0	V
GATE High Threshold	VgH	ΔV _{GATE} - V _{GATE} , decreas	sing		1.0	1.6	2.0	V
PWRGD, PWRGD Output		VPWRGD = 80V, VDRAIN =	= 48V	1			10	
Leakage	Гон	V _{PWRGD} = 80V, V _{DRAIN} =	= OV				10	μΑ
PWRGD Low Voltage (VPWRGD - VEE)	VoL	VDRAIN - VEE < VDL, ISINK (A, E versions)	< = 5r	mA		0.11	0.4	V
PWRGD Low Voltage (VpwRGD - VDRAIN)	Vol	VDRAIN = 5V, ISINK = 5mA	А (В,	F versions)		0.11	0.4	٧
OVERTEMPERATURE PROTECT	ION				•			•
Overtemperature Threshold	T _{OT(TH)}	Junction temperature, ten	mpera	ature rising		135		°C
Overtemperature Hysteresis	T _{HYS}	See Thermal Shutdown se	ectior	า		20		°C
AC PARAMETERS					•			•
OV High to GATE Low	tphlov	Figures 1a, 2			0.5		μs	
UV Low to GATE Low	t _{PHLUV}	Figures 1a, 3			0.4		μs	
OV Low to GATE High	tplhov	Figures 1a, 2			3.3		μs	
UV High to GATE High	tplhuv	Figures 1a, 3				8.4		ms
SENSE High to GATE Low	tphlsense.	Figures 1a, 4a				1		μs
Current Limit to GATE Low	t _{PHLCL}	Time from continuous current limit to GATE shutdown (see <i>Overcurrent</i>		0.35	0.5	0.65	ms	
		Fault Integrator section), Figures 1b, 4b	E	E, F versions	1.4	2.0	2.6	
DRAIN Low to PWRGD Low DRAIN Low to (PWRGD - DRAIN)	to	Figures 1a, 5a; A and E versions		ns		8.2		mo
High	[†] PHLDL	Figures 1a, 5a; B and F versions			8.2		ms	
GATE High to PWRGD Low GATE High to (PWRGD - DRAIN)	to o	Figures 1a, 5b; A and E versions			8.2		ma	
High	^t PHLGH	Figures 1a, 5b; B and F versions			8.2		ms	
TURN-OFF								
Latch-Off Period	toff	(Note 3)	А, В,	E, F versions		128 x tphlcl		ms

- **Note 1:** All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to VEE, unless otherwise specified.
- Note 2: Gate pulldown current after the current limit to GATE low (tPHLCL) time has elapsed.
- **Note 3:** Minimum duration of GATE pulldown following a circuit breaker fault. The MAX5921_ automatically restarts after a circuit breaker fault. The MAX5939_ is latched off and can be reset by toggling UV low. The GATE pulldown does not release until toff has elapsed.
- Note 4: The min/max limits are 100% production tested at +25°C and +85°C and guaranteed by design at -40°C.

Typical Operating Characteristics

 $(V_{DD} = +48V, V_{EE} = 0V, T_A = +25^{\circ}C, unless otherwise noted.)$



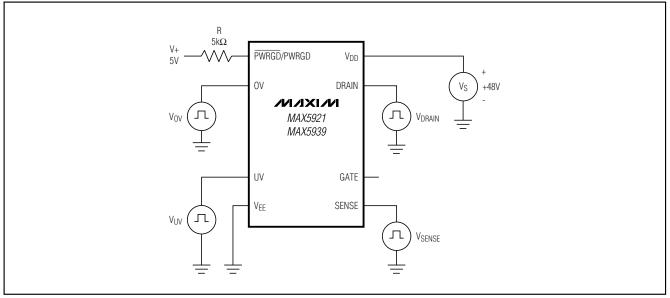


Figure 1a. Test Circuit 1

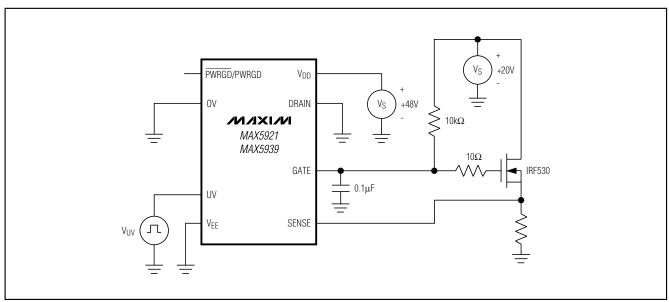


Figure 1b. Test Circuit 2

_Timing Diagrams

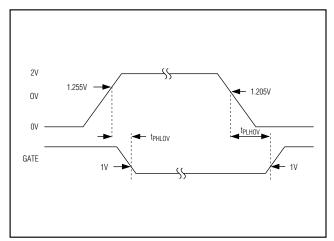


Figure 2. OV to GATE Timing

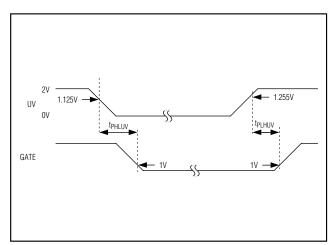


Figure 3. UV to GATE Timing

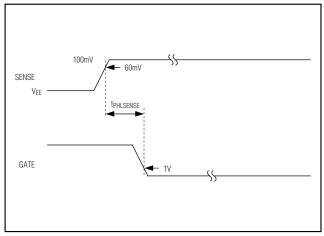


Figure 4a. SENSE to GATE Timing

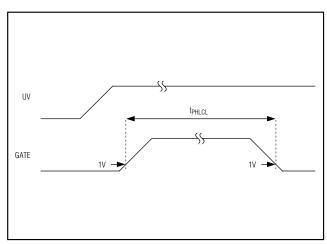


Figure 4b. Active Current-Limit Threshold

Timing Diagrams (continued)

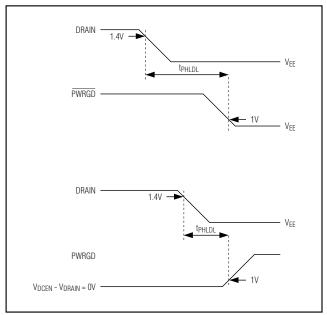


Figure 5a. DRAIN to PWRGD/PWRGD Timing

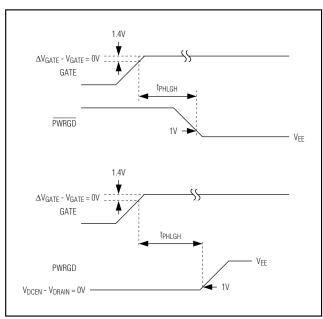
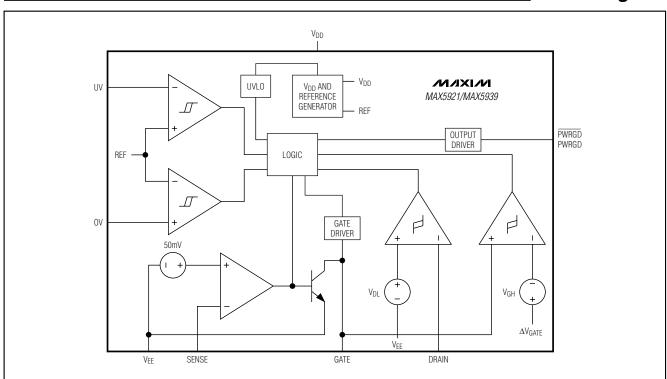


Figure 5b. GATE to PWRGD/PWRGD Timing

Block Diagram



Pin Description

Р	PIN			
MAX5921A/ MAX5921E MAX5939A/ MAX5939E	MAX5921B/ MAX5921F MAX5939B/ MAX5939F	NAME	FUNCTION	
1	l	PWRGD	Power-Good Signal Output. \overline{PWRGD} is an active-low open-drain status output referenced to VEE. \overline{PWRGD} latches low when VDRAIN - VEE \leq VDL and VGATE $> \Delta$ VGATE indicating a power-good condition. \overline{PWRGD} is open drain otherwise.	
	1	PWRGD	Power-Good Signal Output. PWRGD is an active-high open-drain status output referenced to DRAIN. PWRGD latches in a high-impedance state when V_{DRAIN} - $V_{EE} \le V_{DL}$ and $V_{GATE} > \Delta V_{GATE}$ indicating a power-good condition. PWRGD is pulled low to DRAIN otherwise.	
2	2	OV	Overvoltage Detection Input. OV is referenced to V _{EE} . When OV is pulled above V _{OVH} voltage, GATE pulls low. GATE remains low until the OV voltage reduces to V _{OVH} - V _{OVHY} .	
3	3	UV	Undervoltage Detection Input. UV is referenced to VEE. When UV is pulled above VUVH voltage, the GATE is enabled. When UV is pulled below VUVL, GATE pulls low. UV is also used to reset the circuit breaker after a fault condition. To reset the circuit breaker, pull UV below VUVL. The reset command can be issued immediately after a fault condition; however, the device will not restart until a toff delay time has elapsed after the fault condition is removed.	
4	4	VEE	Negative Power-Supply Input. Connect to the negative power-supply rail.	
5	5	SENSE	Current-Sense Input. Connect to the external sense resistor and the source of the external MOSFET. The voltage drop across the external sense resistor is monitored to detect overcurrent or short-circuit fault conditions. Connect SENSE to VEE to disable the current limiting feature.	
6	6	GATE	Gate Drive Output. Connect to the gate of the external N-channel MOSFET.	
7	7	DRAIN	Output Voltage Sense Input. Connect to the output voltage node (drain of external N-channel MOSFET). Place the MAX5921/MAX5939 such that DRAIN is close to the drain of the external MOSFET for the best thermal protection.	
8	8	V _{DD}	Positive Power-Supply Input. This is the power ground in the negative supply voltage system. Connect to the higher potential of the power-supply inputs.	

Detailed Description

The MAX5921/MAX5939 integrated hot-swap controllers for -48V power systems allow circuit boards to be safely hot plugged into a live backplane without causing a glitch on the power-supply rail. When circuit boards are inserted into a live backplane, the bypass capacitors at the input of the board's power module or switching power supply can draw large inrush currents as they charge. Uncontrolled inrush currents can cause glitches on the system power supply and damage components on the board.

The MAX5921/MAX5939 provide a controlled turn-on to circuit cards preventing damage to connectors, board components, and prevent glitches on the power-supply rail. Both the MAX5921/MAX5939 provide undervoltage, overvoltage, and overcurrent protection. The MAX5921/MAX5939 ensure that the input voltage is stable and within tolerance before applying power to the load. The device also provides protection against input voltage steps by limiting the load current to a safe level without turning off power to the load.

Board Insertion

Figure 6a shows a typical hot-swap circuit for -48V systems. When the circuit board first makes contact with the backplane, the DRAIN to GATE capacitance (C_{gd}) of Q1 pulls up the GATE voltage to roughly IVEE x ($C_{gd}/C_{gd}+C_{gs}$)I. The MAX5921/MAX5939 feature an internal dynamic clamp between GATE and VEE to keep the gate-to-source voltage of Q1 low during hot insertion preventing Q1 from passing an uncontrolled current to the load. For most applications, the internal clamp between GATE and VEE of the MAX5921/MAX5939 eliminates the need for an external gate-to-source capacitor. The resistor R3 limits the current into the clamp circuitry during card insertion.

Power-Supply Ramping

The MAX5921/MAX5939 can reside either on the backplane or the removable circuit board (Figure 6a). Power is delivered to the load by placing an external N-channel MOSFET pass transistor in the power-supply path.

After the circuit board is inserted into the backplane, and the supply voltage at VEE is stable and within the undervoltage and overvoltage tolerance, the MAX5921/MAX5939 gradually turn on the external MOSFET by charging the gate of Q1 with a 45 μ A current source. Capacitor C2 provides a feedback signal to accurately limit the inrush current.

The inrush current can be calculated:

INRUSH = IPU x CL / C2

where C_L is the total load capacitance, C3 + C4, and I_{PU} is the gate pullup current.

Figure 6b shows the inrush current waveform. The current through C2 controls the GATE voltage. At the end of the DRAIN ramp, the GATE voltage is charged to its final value. The GATE-to-SENSE clamp limits the maximum $\Delta V_{\rm GATE}$ to 18V.

Board Removal

If the circuit card is removed from the backplane, the voltage at the UV falls below the UVLO detect threshold, and the MAX5921/MAX5939 turn off the external MOSFET.

Current Limit and Electronic Circuit Breaker

The MAX5921/MAX5939 provide current-limiting and circuit-breaker features that protect against excessive load current and short-circuit conditions. The load current is monitored by sensing the voltage across an external sense resistor connected between VEE and SENSE.

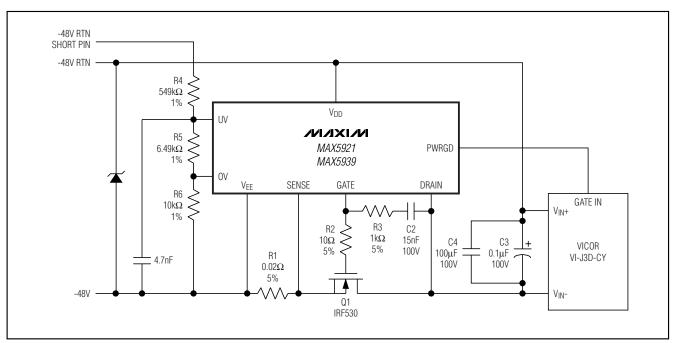


Figure 6a. Inrush Control Circuitry/Typical Application Circuit

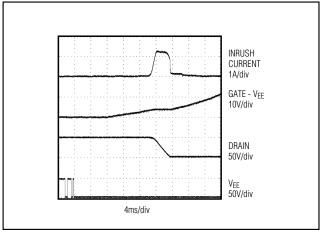


Figure 6b. Inrush Control Waveforms

If the voltage between VEE and SENSE reaches the current-limit trip voltage (VCL), the MAX5921/MAX5939 pull down the GATE and regulate the current through the external MOSFET such that VSENSE - VEE \leq VCL. If the current drawn by the load drops below VCL / RSENSE limit, the GATE voltage rises again. However, if the load current is at the regulation limit of VCL / RSENSE for a period of tpHLCL, the electronic circuit breaker trips, causing the MAX5921/MAX5939 to turn off the external MOSFET.

After an overcurrent fault condition, the MAX5921 automatically restarts after tOFF has elapsed. The MAX5939 circuit breaker is reset by toggling UV or by cycling power. Unless power is cycled to the MAX5939, the device waits until tOFF has elapsed before turning on the gate of the external FET.

Load-Current Regulation

The MAX5921/MAX5939 accomplish load-current regulation by pulling current from GATE whenever VSENSE - VEE > VCL. This decreases the gate-to-source voltage of the external MOSFET, thereby reducing the load current. When VSENSE - VEE < VCL, the MAX5921/MAX5939 pulls GATE high by a $45\mu\text{A}$ (IPU) current.

Exponential Current Regulation

The MAX5921/MAX5939 provide an exponential pull-down current to turn off the external FET in response to overcurrent conditions. The GATE pulldown current increases (see *Typical Operating Characteristics*) in response to VSENSE - VEE potentials greater than 50mV (VCL).

Load Current Regulation (Short-Circuit Condition)

The MAX5921/MAX5939 devices also include a very fast high-current pulldown source connected to GATE (see *Typical Operating Characteristics*). The high-current pulldown activates if VSENSE exceeds VEE by 650mV (typ) during a catastrophic overcurrent or short-circuit fault condition. The high-current pulldown circuit sinks as much as 450mA from GATE to turn off the external MOSFET.

Immunity to Input Voltage Steps

The MAX5921/MAX5939 guard against input voltage steps on the input supply. A rapid increase in the input supply voltage (VDD - VEE increasing) causes a current step equal to $I = C_L \times \Delta V_{IN} / \Delta t$, proportional to the input voltage slew rate (ΔV_{IN} / Δt). If the load current exceeds VCI / RSENSE during an input voltage step, the MAX5921/ MAX5939 current limit activates, pulling down the gate voltage and limiting the load current to VCL / RSENSE. The DRAIN voltage (VDRAIN) then slews at a slower rate than the input voltage. As the drain voltage starts to slew down, the drain-to-gate feedback capacitor C2 pushes back on the gate, reducing the gate-to-source voltage (VGS) and the current through the external MOSFET. Once the input supply reaches its final value, the DRAIN slew rate (and therefore the inrush current) is limited by the capacitor C2 just as it is limited in the startup condition (see the *Power-Supply Ramping* section). To ensure correct operation, RSENSE must be chosen to provide a current limit larger than the sum of the load current and the dynamic current into the load capacitance in the slewing mode.

If the load current plus the capacitive charging current is below the current limit, the circuit breaker does not trip.

Undervoltage and Overvoltage Protection

Use UV and OV to detect undervoltage and overvoltage conditions. UV and OV internally connect to analog comparators with 130mV (UV) and 50mV (OV) of hysteresis. When the UV voltage falls below its threshold or the OV voltage rises above its threshold, GATE pulls low. GATE is held low until UV goes high and OV is low, indicating that the input supply voltage is within specification. The MAX5921/MAX5939 includes an internal lockout (UVLO) that keeps the external MOSFET off until the input supply voltage exceeds 15.4V, regardless of the UV input.

UV is also used to reset the circuit breaker after a fault condition has occurred. Pull UV below V_{UVL} to reset the circuit breaker.

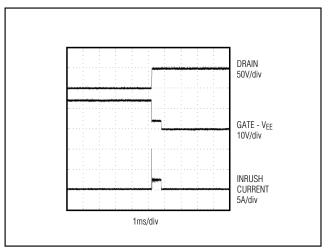


Figure 7. Short-Circuit Protection Waveform

Figure 10 shows how to program the undervoltage and overvoltage trip thresholds using three resistors. With R4 = $549k\Omega$, R5 = $6.49k\Omega$, and R6 = $10k\Omega$, the undervoltage threshold is set to 38.5V (with a 43V release from undervoltage), and the overvoltage is set to 71V. The resistor-divider also increases the hysteresis and overvoltage lockout to 4.5V and 2.8V at the input supply, respectively.

PWRGD/PWRGD Output

Use the PWRGD (PWRGD) output to enable a power module after hot insertion. Use the MAX59_A (PWRGD) to enable modules with an active-low enable input (Figure 12), or use the MAX59_B (PWRGD) to enable modules with an active-high enable input (Figure 11).

The PWRGD signal is referenced to the DRAIN terminal, which is the negative supply of the power module. The $\overline{\text{PWRGD}}$ signal is referenced to V_{EE} .

When the DRAIN voltage of the MAX5921A (see Selector Guide for complete selection) or MAX5939A is high with respect to VEE or the GATE voltage is low from an undervoltage condition, then the internal pull-down MOSFET Q2 is off. The \overline{PWRGD} output goes into a high-impedance state (Figure 13). \overline{PWRGD} is pulled high by the module's internal pullup current source, turning the module off. When the DRAIN voltage drops below VDL and the GATE voltage is greater than $\Delta VGATE$ - VGH, Q2 turns on and \overline{PWRGD} pulls low, enabling the module.

The PWRGD signal can also be used to turn on an LED

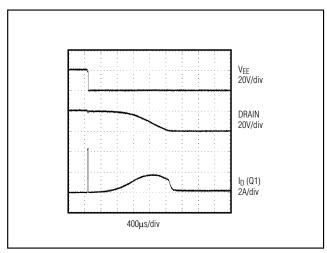


Figure 8. Voltage Step-On Input Supply

or optoisolator to indicate that the power is good (Figure 13) (see the *Component Selection Procedure* section).

When the DRAIN voltage drops below V_{DL} and the GATE voltage is greater than ΔV_{GATE} - V_{GH} , MOSFET Q3 turns on, shorting I_1 to V_{EE} and turning Q2 off. The pullup current in the module pulls the PWRGD high, enabling the module.

When the DRAIN voltage of the MAX5921B/MAX5939B (see *Selector Guide* for complete selection) is high with respect to VEE (Figure 12) or the GATE voltage is low due to an undervoltage condition, the internal MOSFET Q3 is turned off so that I₁ and the internal MOSFET Q2 clamp PWRGD to the DRAIN turning off the module.

Once the PWRGD and PWRGD outputs are active, the MAX5921/MAX5939 output does not toggle due to an overvoltage (OV) fault.

GATE Voltage Regulation

GATE goes high when the following startup conditions are met: UV is high, OV is low, the supply voltage is above VUVLOH, and (VSENSE - VEE) is less than 50mV. The gate is pulled up with a 45µA current source and is regulated at 13.5V above VEE. The MAX5921/MAX5939 include an internal clamp that ensures the GATE voltage of the external MOSFET never exceeds 18V. During a fast-rising VDD, an additional dynamic clamp keeps the GATE and SENSE potentials as close as possible to prevent the FET from accidentally turning on. When a fault condition is detected, GATE is pulled low (see the *Load Current Regulation* section).

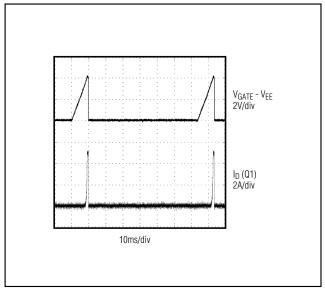


Figure 9. Automatic Restart After a Short Circuit

Overcurrent Fault Integrator

The MAX5921/MAX5939 feature an overcurrent fault integrator. When an overcurrent condition is detected, an internal digital counter is incremented. The clock period for the digital counter is 32µs for the 500µs maximum current-limit duration version and 128µs for 2ms maximum current-limit duration devices. An overcurrent of less than 32µs is interpreted as an overcurrent of 32µs. When the counter reaches 500µs (the maximum currentlimit duration) for the MAX5921/MAX5939A, an overcurrent fault is generated. If the overcurrent fault does not last 500µs, then the counter begins decrementing at a rate 128 (maximum current-limit duty cycle) times slower than the counter was incrementing. Repeated overcurrent conditions generate a fault if the duty cycle of the overcurrent condition duty ratio is greater than the maximum current-limit duty cycle (see Figure 14).

Thermal Shutdown

The MAX5921/MAX5939 include internal die-temperature monitoring. When the die temperature reaches the thermal-shutdown threshold, Tot, the MAX5921/MAX5939 pull GATE low and turn off the external MOSFET. If a good thermal path is provided between the MOSFET and the MAX5921/MAX5939, the device offers thermal protection for the external MOSFET. Placing the

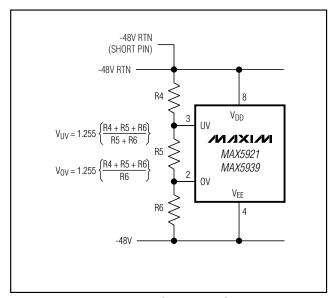


Figure 10. Undervoltage and Overvoltage Sensing

MAX5921/MAX5939 near the drain of the external MOS-FET offers the best thermal protection because most of the power is dissipated in its drain.

After a thermal shutdown fault has occurred, the MAX5921_ turns the external FET off for a minimum time of toff, allowing the MOSFET to cool down. The MAX5921_ device restarts after the temperature drops 20°C below the thermal-shutdown threshold.

The MAX5939_ latches off after a thermal shutdown fault. The MAX5939_ can be restarted by toggling UV low or cycling power. However, the device keeps the external FET off for a minimum time of toff when toggling UV.

Applications Information_ Sense Resistor

The circuit-breaker current-limit threshold is set to 50mV (typ). Select a sense resistor that causes a drop equal to or above the current-limit threshold at a current level above the maximum normal operating current. Typically, set the overload current to 1.5 to 2.0 times the nominal load current plus the dynamic load-capacitance charging current during startup. Choose the sense resistor power rating to be greater than (VCL)² / RSENSE.

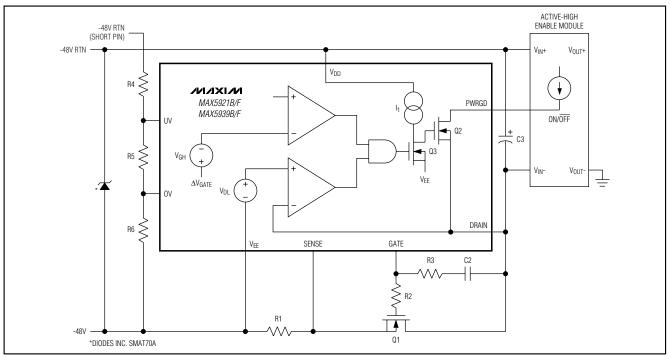


Figure 11. Active-High Enable Module

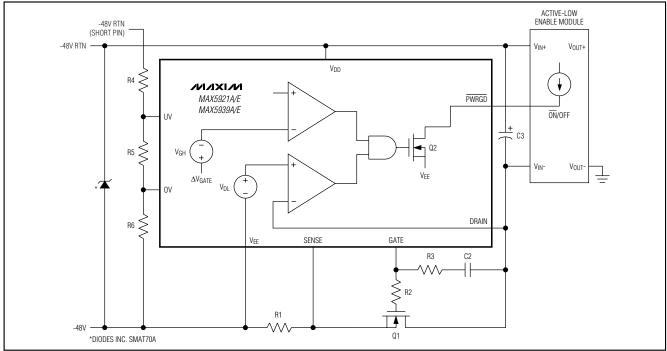


Figure 12. Active-Low Enable Module

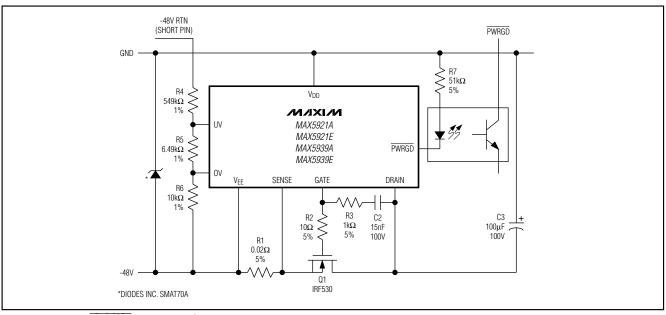


Figure 13. Using PWRGD to Drive an Optoisolator

Component Selection Procedure:

- Determine load capacitance:
 - C_L = C2 + C3 + module input capacitance
- Determine load current, ILOAD.
- Select circuit-breaker current, for example:

• Calculate RSENSE:

$$R_{SENSE} = \frac{50 \text{mV}}{I_{CB}}$$

Realize that I_{CB} varies ±20% due to trip-voltage tolerance.

• Set allowable inrush current:

$$I_{INRUSH} \le 0.8 \times \frac{40 \text{mV}}{R_{SENSE}} - I_{LOAD} \text{ or}$$

 $I_{INRUSH} + I_{LOAD} \le 0.8 \times I_{CB(MIN)}$

• Determine value of C2:

$$C2 = \frac{45\mu A \times C_L}{I_{INRUSH}}$$

• Calculate value of C1:

$$C1 = (C2 + C_{gd}) \times \left(\frac{VIN(MAX) - VGS(TH)}{VGS(TH)} \right)$$

• Determine value of R3:

$$R3 = \frac{150\mu s}{C2}$$

- Set R2 = 10Ω .
- If an optocoupler is utilized as in Figure 14, determine the LED series resistor:

$$R7 = \frac{V_{IN(NOMINAL)} - 2V}{3 \le I_{IFD} \le 5mA}$$

Although the suggested optocoupler is not specified for operation below 5mA, its performance is adequate for 36V temporary low-line voltage where LED current would then be ≈ 2.2 mA to 3.7mA. If R7 is set as high as 51k Ω , optocoupler operation should be verified over the expected temperature and input voltage range to ensure suitable operation when LED current ≈ 0.9 mA for 48V input and ≈ 0.7 mA for 36V input.

If input transients are expected to momentarily raise the input voltage to >100V, select an input transient-voltage-suppression diode (TVS) to limit maximum voltage on the MAX5921/MAX5939 to less than 100V. A suitable device is the Diodes Inc. SMAT70A telecom-specific TVS.

Select Q1 to meet supply voltage, load current, efficiency, and Q1 package power-dissipation requirements:

$$BV_{DSS} \ge 100V$$
 $I_{D(ON)} \ge 3 \times I_{LOAD}$
 $DPAK, D^2PAK, or TO-220AB$

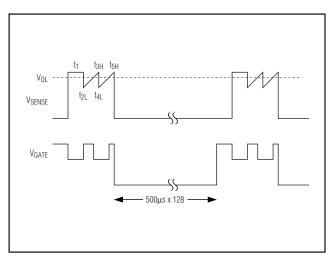


Figure 14. MAX5921A Overcurrent Fault Example

The lowest practical R_{DS(ON)}, within budget constraints and with values from $14m\Omega$ to $540m\Omega$, are available at 100V breakdown.

Ensure that the temperature rise of Q1 junction is not excessive at normal load current for the package selected. Ensure that ICB current during voltage transients does not exceed allowable transient-safe operating-area limitations. This is determined from the SOA and transient-thermal-resistance curves in the Q1 manufacturer's data sheet.

Example 1:

 $I_{LOAD}=2.5A,$ efficiency = 98%, then $V_{DS}=0.96V$ is acceptable, or $R_{DS(ON)} \leq 384 m\Omega$ at operating temperature is acceptable. An IRL520NS 100V NMOS with RDS(ON) $\leq 180 m\Omega$ and $I_{D(ON)}=10A$ is available in D²PAK. (A Vishay Siliconix SUD40N10-25 100V NMOS with RDS(ON) $\leq 25 m\Omega$ and $I_{D(ON)}=40A$ is available in DPAK but may be more costly because of a larger die size).

Using the IRL520NS, V_{DS} \leq 0.625V even at +80°C so efficiency \geq 98.6% at 80°C. P_D \leq 1.56W and junction temperature rise above case temperature would be 5°C due to the package $\theta_{JC} = 3.1$ °C/W thermal resistance. Of course, using the SUD40N10-25 will yield an efficiency greater than 99.8% to compensate for the increased cost.

If I_{CB} is set to twice I_{LOAD}, or 5A, V_{DS} momentarily doubles to \leq 1.25V. If C_{OUT} = 4000µF, transient-line input voltage is $\Delta 36$ V, the 5A charging-current pulse is:

$$t = \frac{4000\mu F \times 1.25V}{5A} = 1ms$$

Entering the data sheet transient-thermal-resistance curves at 1ms provides a $\theta_{JC}=0.9^{\circ}$ C/W. PD = 6.25W, so $\Delta t_{JC}=5.6^{\circ}$ C. Clearly, this is not a problem.

Example 2:

I_{LOAD} = 10A, efficiency = 98%, allowing V_{DS} = 0.96V but R_{DS(ON)} \leq 96m Ω . An IRF530 in a D²PAK exhibits R_{DS(ON)} \leq 90m Ω at +25°C and \leq 135m Ω at +80°C. Power dissipation is 9.6W at +25°C or 14.4W at +80°C. Junction-to-case thermal resistance is 1.9W/°C, so the junction temperature rise would be approximately 5°C above the +25°C case temperature. For higher efficiency, consider IRL540NS with R_{DS(ON)} \leq 44m Ω . This allows η = 99%, P_D \leq 4.4W, and T_{JC} = +4°C (θ _{JC} = 1.1°C/W) at +25°C.

Thermal calculations for the transient condition yield I_{CB} = 20A, V_{DS} = 1.8V, t = 0.5ms, transient θ _{JC} = 0.12°C/W, P_D = 36W and Δ t_{JC} = 4.3°C.

Lavout Guidelines

Good thermal contact between the MAX5921/MAX5939 and the external MOSFET is essential for the thermal-shutdown feature to operate effectively. Place the MAX5921/MAX5939 as close as possible to the drain of the external MOSFET and use wide circuit-board traces for good heat transfer. See Figure 15 for an example of recommended layout for Kelvin-sensing current through a sense resistor on a PC board.

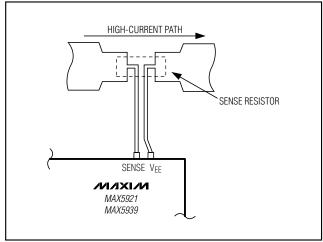


Figure 15. Recommended Layout for Kelvin-Sensing Current Through Sense Resistor

Selector Guide

PART	DCEN POLARITY	FAULT MANAGEMENT	MAXIMUM CURRENT-LIMIT DURATION (ms)	MAXIMUM CURRENT-LIMIT DUTY CYCLE
MAX5921AESA	Active-Low PWRGD	Autoretry	0.5	1/128
MAX5921BESA	Active-High PWRGD	Autoretry	0.5	1/128
MAX5921EESA	Active-Low PWRGD	Autoretry	2	1/128
MAX5921FESA	Active-High PWRGD	Autoretry	2	1/128
MAX5939AESA	Active-Low PWRGD	Latched	0.5	1/128
MAX5939BESA	Active-High PWRGD	Latched	0.5	1/128
MAX5939EESA	Active-Low PWRGD	Latched	2	1/128
MAX5939FESA	Active-High PWRGD	Latched	2	1/128

Ordering Information (continued)

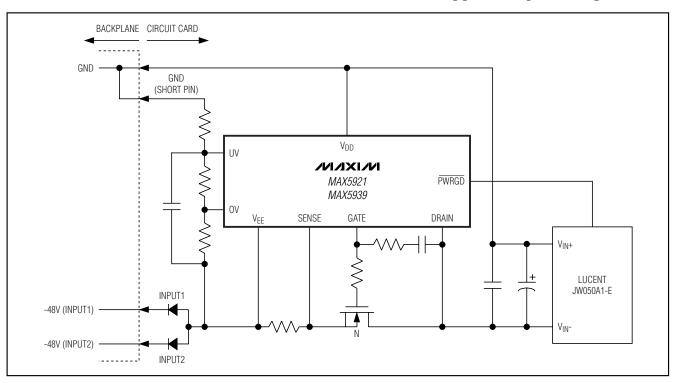
PART	TEMP RANGE	PIN-PACKAGE
MAX5921EESA*	-40°C to +85°C	8 SO
MAX5921FESA*	-40°C to +85°C	8 SO
MAX5939AESA	-40°C to +85°C	8 SO
MAX5939BESA	-40°C to +85°C	8 SO
MAX5939EESA*	-40°C to +85°C	8 SO
MAX5939FESA*	-40°C to +85°C	8 SO

^{*}Future product—contact factory for availability.

Chip Information

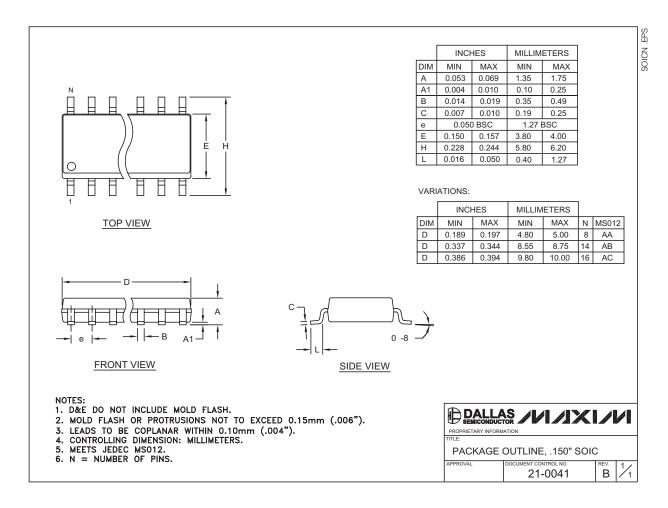
TRANSISTOR COUNT: 2645
PROCESS: BICMOS

Typical Operating Circuit



Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)



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